

5/16/06

<b>FORM PTO-1449</b>  <b>U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>	<b>Atty. Docket No.</b>  <b>Applicant</b> Kangguo CHENG et al.	<b>Application No.</b> 10/710,608
<b>INFORMATION DISCLOSURE STATEMENT</b> <b>BY APPLICANT</b> (Use several sheets if necessary)	<b>Filing Date</b> 07/23/2004	<b>Group</b> 2812

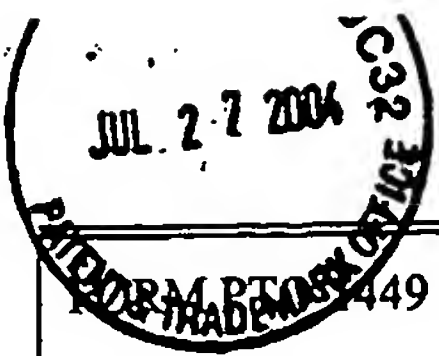
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mm		US 2002/0063292 A1	5-30-2002	Armstrong et al.			
		US 2003/0032261 A1	2-13-2003	Yeh et al.			
		US 2003/0040158 A1	2-27-2003	Saitoh			
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		7,015,082	3-21-2006	Doris et al.			
	6,974,981	12-13-2005	Chidambarrao et al.				
mm		6,977,194	12-20-2005	Belyansky et al.			

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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
mm		JP 64-76755	3-22-1989	Japan			
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER <i>mm</i>				DATE CONSIDERED 11/9/06			

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.	Application No.	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)				Applicant		
				Filing Date	Group	
<b>U.S. PATENT DOCUMENTS</b>						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS
<b>FOREIGN PATENT DOCUMENTS</b>						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>						
		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.				
		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." 1989 IEEE, Paper 6.2, pp. 140-143.				
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		J.H. Van Der Merwe, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.				
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		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050				
	D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462					
	Q. Quyang et al., "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFET with Enhanced Device Performance and Scalability". 2000, IEEE, pp. 151-154.					
EXAMINER				DATE CONSIDERED 11/9/06		
*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.						



FORM PTO 449 (Modified)  LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	ATTY. DOCKET NO. FIS920040150US1	SERIAL NO. 10/710,608
	APPLICANT: Kangguo CHENG, <i>et al.</i>	
(Use several sheets if necessary)	FILING DATE: 07/23/2004	GROUP: Unassigned

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
M-J	6,228,694 B1	5/8/2001	Doyle et al.			
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	6,281,532 B1	8/28/2001	Doyle et al.			
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nm	US 2002/0086472 A1	7/4/2002	Roberds et al.			
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	6,506,652	01/14/03	Jan et al.			

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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## OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

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FORM PTO-1449 (Modified)

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.  
FIS920040150US1SERIAL NO.  
10/710,608APPLICANT:  
Kangguo CHENG, *et al.*FILING DATE:  
07/23/04GROUP:  
Unassigned

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
M-9	5,081,513	1/14/1992	Jackson, et al.			
	3,602,841	8/31/1971	McGroddy			
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	6,133,071	10/17/2000	Nagai			
	6,046,464	4/4/2000	Schetzina			
MM	6,025,280	2/15/2000	Brady, et al.			

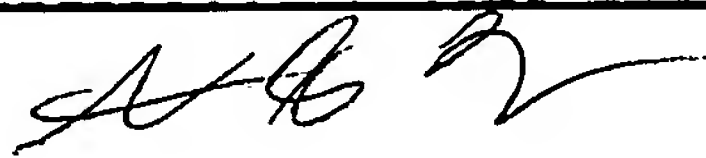
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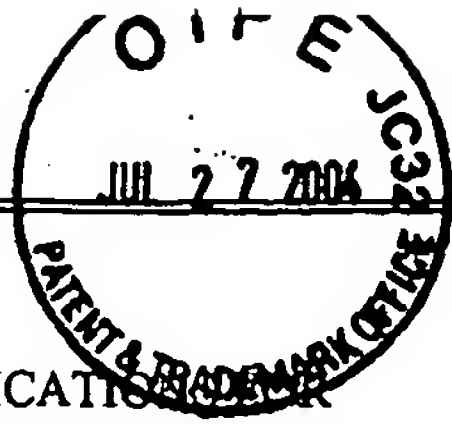


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LIST OF PATENTS AND PUBLICATIONS APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT: Kangguo CHENG, <i>et al.</i>	
(Use several sheets if necessary)	FILING DATE: 07/23/04	GROUP: Unassigned

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
<i>MA</i>	5,940,736	8/17/1999	Brady, et al.			
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	5,060,030	10/22/1991	Hoke			
	4,958,213	9/18/1990	Eklund, et al.			
<i>MA</i>	4,665,415	5/12/1987	Esaki, et al.			

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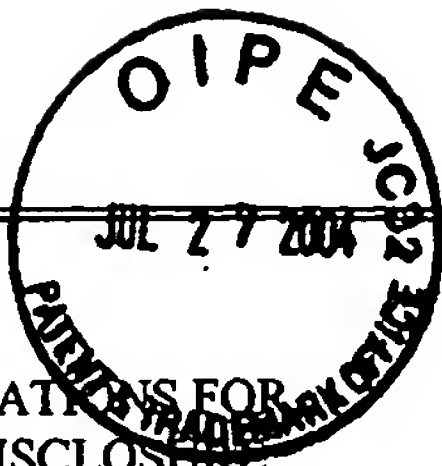
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EM	5,989,978	11/23/1999	Peidous				
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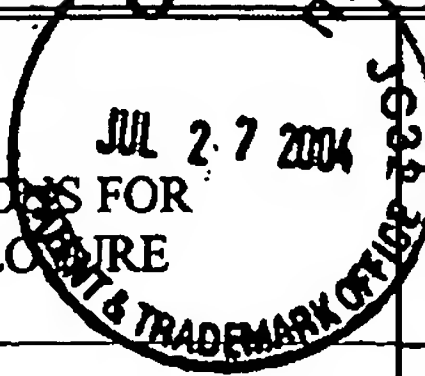
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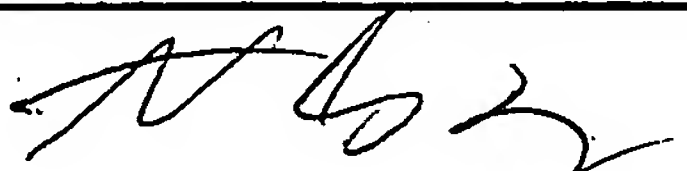
  

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Mg		5,557,122	9/17/1996	Shrivastava, et al.			
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MM		6,319,794	11-20-2001	Akatsu et al.			
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Form PTO-1449 (Modified)

Attorney Docket No.:  
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10/710,608LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S  
INFORMATION DISCLOSURE STATEMENTApplicant:  
Kangguo CHENG, *et al.*

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Page 1 of 1

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07/23/04Group:  
Unassigned

## REFERENCE DESIGNATION

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EXAMINERS INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

## FOREIGN PATENT DOCUMENTS

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## OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

MA		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si <i>n</i> -MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
1		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
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EXAMINER

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<b>INFORMATION DISCLOSURE CITATION</b> <i>(On several sheets if necessary)</i>				Docket Number (Optional)		Application Number	
				FIS920040150US1		10/710,608	
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				Cheng, et al.			
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MM		3,602,841	8-31-71	McGroddy			
		4,665,415	5-12-87	Esaki, et al.			
		4,853,076	8-1-89	Tsaur, et al.			
		4,855,245	8-8-89	Neppl, et al.			
MM		4,952,524	8-28-90	Lee, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
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MM		US 2001/0009784 A1	7-26-01	Ma, et al.			
		US 2002/0063292 A1	5-30-02	Armstrong, et al.			
		US 2002/0074598 A1	6-20-02	Doyle, et al.			
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MM		JP64-76755	03-1989	Japan				

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
MM		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs". International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
MM		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs." 2002 Symposium on VLSI Technology Digest of Technical Papers, IEEE, pp. 98-99.

EXAMINER <span style="font-family: cursive;">TSV</span>	DATE CONSIDERED <span style="font-family: cursive;">11/7/00</span>
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**INFORMATION DISCLOSURE CITATION**  
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1/9		4,958,213	9-18-90	Eklund, et al.			
1		5,006,913	4-9-91	Sugahara, et al.			
		5,060,030	10-22-91	Hoke, et al.			
		5,081,513	1-14-92	Jackson, et al.			
1/1		5,108,843	4-28-92	Ohtaka, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
1/1		US 2002/0086497 A1	7-4-02	Kwok			
		US 2002/0090791 A1	7-11-02	Doyle, et al.			
		US 2003/0032261 A1	2-13-03	Yeh, et al.			
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1/9		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress." International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
1/9		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm Node CMOS Technology for Large Scale System-on-a-Chip Application." International Electron Devices Meeting, 23.5.1, IEEE, April 2000.

EXAMINER

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11/9/04

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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	Docket Number (Optional) FIS920040150US1	Application Number 10/710,608
	Applicant(s) Cheng, et al.	
	Filing Date 7/23/04	Group Art Unit 2812

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mm		5,134,085	7-28-92	Gilgen, et al.			
		5,310,446	5-10-94	Konishi, et al.			
		5,354,695	10-11-94	Leedy			
		5,371,399	12-6-94	Burroughes, et al.			
mm		5,391,510	2-21-95	Hsu, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
mm		US 2003/0057184 A1	3-27-03	Yu, et al.			
mm		US 2003/0067035 A1	4-10-03	Tews, et al.			

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

mm		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design." International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
mm		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement." International Electron Devices Meeting, IEEE, March 2001.

EXAMINER <span style="float: right; text-align: right;">mm</span>	DATE CONSIDERED <span style="float: right; text-align: right;">11/9/00</span>
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	Filing Date 7/23/04	Group Art Unit 2812

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MJ		5,459,346	10-17-95	Asakawa, et al.			
		5,471,948	12-5-95	Burroughes, et al.			
		5,557,122	9-17-96	Shrivastava, et al.			
		5,561,302	10-1-96	Candelaria			
		5,565,697	10-15-96	Asakawa, et al.			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

MJ		K. Ota, et al., "Novel Locally Strained Channel Technique for High Performance 55nm CMOS." International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
MH		G. Zhang, et al., "A New 'Mixed-Mode' Reliability Degradation Mechanism in Advanced Si and SiGe Bipolar Transistors." IEEE Transactions on Electron Devices, vol. 49, no. 12, December 2002, pp. 2151-56.

EXAMINER		DATE CONSIDERED	11/9/05
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**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M9		5,571,741	11-5-96	Leedy			
		5,592,007	1-7-97	Leedy			
		5,592,018	1-7-97	Leedy			
		5,670,798	9-23-97	Schetzina			
M9		5,679,965	10-21-97	Schetzina			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

M9		H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143.
M9		C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

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				Applicant(s) Cheng, et al.				
				Filing Date 7/23/04		Group Art Unit 2812		
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
		5,683,934	11-4-97	Candelaria				
		5,840,593	11-24-98	Leedy				
		5,861,651	1-19-99	Brasen, et al.				
		5,880,040	3-9-99	Sun, et al.				
		5,940,716	8-17-99	Jin, et al.				
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<b>FOREIGN PATENT DOCUMENTS</b>								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
		S.R. Sheng, et al., "Degradation and Recovery of SiGe HBTs Following Radiation and Hot-Carrier Stressing." Pp. 14-15.						
		Z. Yang, et al., "Avalanche Current Induced Hot Carrier Degradation in 200 GHz SiGe Heterojunction Bipolar Transistors." Pp. 1-5.						
EXAMINER				DATE CONSIDERED				
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				Applicant(s) Cheng, et al.			
				Filing Date		Group Art Unit	
				7/23/04		2812	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,940,736	8-17-99	Brady, et al.			
		5,946,559	8-31-99	Leedy			
		5,960,297	9-28-99	Saki			
		5,989,978	11-23-99	Peidous			
		6,008,126	12-28-99	Leedy			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
		H. Li, et al., "Design of W-Band VCOs with High Output Power for Potential Application in 77 GHz Automotive Radar Systems." 2003 IEEE GaAs Digest, pp. 263-66.
		H. Wurzer, et al., "Annealing of Degraded npn-Transistors- Mechanisms and Modeling." IEEE Transactions on Electron Devices, vol. 41, no. 4, April 1994, pp. 533-38.

EXAMINER	DATE CONSIDERED 11/4/04
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				FIS920040150US1		10/710,608	
				Applicant(s) Cheng, et al.			
				Filing Date 7/23/04		Group Art Unit 2812	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MM		6,025,280	2-15-00	Brady, et al.			
		6,046,464	4-4-00	Schetzina			
		6,066,545	5-23-00	Doshi, et al.			
		6,090,684	7-18-00	Ishitsuka, et al.			
MM		6,107,143	8-22-00	Park, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REP	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
MM		B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40.	
MM		H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.	

EXAMINER	DATE CONSIDERED
	11/4/04

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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional)		Application Number	
				FIS920040150US1		10/710,608	
				Applicant(s)			
				Cheng, et al.			
				Filing Date		Group Art Unit	
				7/23/04		2812	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,117,722	9-12-00	Wuu, et al.			
		6,133,071	10-17-00	Nagai			
		6,165,383	12-26-00	Chou			
		6,221,735	4-24-01	Manley, et al.			
		6,228,694	5-8-01	Doyle, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
		M. Khater, et al., "SiGe HBT Technology with Fmax/Ft = 350/300 GHz and Gate Delay Below 3.3 ps". 2004 IEEE, 4 pages.	
		J.C. Bean, et al., "GEx Si 1-x/Si Strained-Layer Superlattice Grown by Molecular Beam Epitaxy". J. Vac. Sci. Technol. A 2(2), Apr.-June 1984, pp. 436-440.	

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	Filing Date 7/23/04	Group Art Unit 2812

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M-A		6,246,095	6-12-01	Brady, et al.			
		6,255,169	7-3-01	Li, et al.			
		6,261,964	7-17-01	Wu, et al.			
		6,265,317	7-24-01	Chiu, et al.			
M-A		6,274,444	8-14-01	Wang			

U.S. PATENT APPLICATION PUBLICATIONS							
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FOREIGN PATENT DOCUMENTS								
	REP	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
M-A		J.H. Van Der Merve, "Regular Articles". Journal of Applied Physics, Volume 34, No. 1, January 1963, pp. 117-122.	
AM		J.W. Matthews, et al., "Defects in Epitaxial Multilayers". Journal of Crystal Growth 27 (1974), pp. 118-125.	

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				Applicant(s)			
				Cheng, et al.			
				Filing Date		Group Art Unit	
				7/23/04		2812	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,281,532	8-28-01	Doyle, et al.			
		6,284,623	9-4-01	Zhang, et al.			
		6,284,626	9-4-01	Kim			
		6,319,794	11-20-01	Akatsu, et al.			
		6,361,885	3-26-02	Chou			

U.S. PATENT APPLICATION PUBLICATIONS							
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FOREIGN PATENT DOCUMENTS								
	REP	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
		Subramanian S. Iyer, et al., "Heterojunction Bipolar Transistors Using Si-Ge Alloys". IEEE Transactions on Electron Devices, Vol. 36, No. 10, October 1989, pp. 2043-2064.	
		R.H.M. Van De Leur, et al., "Critical Thickness for Pseudomorphic Growth of Si/Ge Alloys and Superlattices". J. Appl. Phys. 64 (6), 15 September 1988, pp. 3043-3050.	

EXAMINER	DATE CONSIDERED 11/9/00
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MM		6,362,082	3-26-02	Doyle, et al.			
		6,368,931	4-9-02	Kuhn, et al.			
		6,403,486	6-11-02	Lou			
		6,403,975	6-11-02	Brunner, et al.			
		6,406,973	6-18-02	Lee			

U.S. PATENT APPLICATION PUBLICATIONS							
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FOREIGN PATENT DOCUMENTS								
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							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)
MM		D.C. Houghton, et al., "Equilibrium Critical Thickness for Si 1-x GEx Strained Layers on (100) Si". Appl. Phys. Lett. 56 (5), 29 January 1990, pp. 460-462.	

EXAMINER	DATE CONSIDERED
	11/14/06

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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		6,461,936	10-8-02	von Ehrenwall			
		6,476,462	11-5-02	Shimizu, et al.			
		6,483,171	11-19-02	Forbes, et al.			
		6,493,497	12-10-02	Ramdani, et al.			
		6,498,358	12-24-02	Lach, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
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FOREIGN PATENT DOCUMENTS								
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				Cheng, et al.			
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EM		6,501,121	12-31-02	Yu, et al.			
		6,506,652	1-14-03	Jan, et al.			
		6,509,618	1-21-03	Jan, et al.			
		6,521,964	2-18-03	Jan, et al.			
		6,531,369	3-11-03	Ozkan, et al.			

U.S. PATENT APPLICATION PUBLICATIONS							
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<b>U.S. PATENT DOCUMENTS</b>								
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M		6,531,740	3-11-03	Bosco, et al.				
		6,621,392	9-16-03	Volant, et al.				
		6,635,506	10-21-03	Volant, et al.				
M		6,831,292	12-14-04	Currie, et al.				
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>								
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							YES	NO
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EXAMINER				DATE CONSIDERED				
M				7/10/2006				
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